



U.S. DEPARTMENT OF COMMERCE

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ATTY. DOCKET NO.	APPLN. NO.
ELM/001 Cont. 10	10/700,429
APPLICANTS	CONF. NO.
Glenn J. Leedy	5639
FILING DATE	GROUP ART UNIT
November 9, 2003	3729

•	U.S. PATENT DOCUMENTS								
EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE			
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EXAMINER INITIAL	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
	NUMBER					YES	NO
G	DE 32 33 195	03/17/83	Germany				
,	JP S60-126871	07/06/85	Japan				
	JP S63-229862	09/26/88	Japan				
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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Complete if known Substitute for form 1449/PTO **Application Number** 10/700,429 Filing Date November 3, 2003 INFORMATION DISCLOSURE **First Named Inventor** Glenn J. Leedy STATEMENT BY APPLICANT Art Unit 3729 **Examiner Name** Carl J. Arbes (use as many sheets as necessary) of **Attorney Docket Number** ELM-1 CONT.10 Sheet

	U.S. PATENT DOCUMENTS							
Examiner Cite		Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages or Relevant			
initials*	No.1	Number – Kind Code ² (if known)	MM-OD-YYYY	Applicant of Cited Documents	Figures Appear			
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				Application Number	10/700,429 (Conf. No.: 5639)	
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STATEMENT BY APPLICANT		First Named Inventor	Glenn J. Leedy			
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4		WO 03/078305	09/25/2003	Viefers et al.					
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NON PATENT LITERATURE DOCUMENTS							
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SI		Phys. Rev., B, Condens, Matter Mater. Phys. (USA), Physical Review B (Condensed Matter and Materials Physics), 15 March 2003, APS through AIP, USA.					
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Complete if known Substitute for form 1449/PTO **Application Number** 10/700,429 (Conf. No.: 5639) INFORMATION DISCLOSURE Filing Date November 3, 2003 First Named Inventor Glenn J. Leedy STATEMENT BY APPLICANT Art Unit 3729 **Examiner Name** Carl J. Arbes (use as many sheets as necessary) Sheet ELM-1 CONT.10 **Attorney Docket Number**

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- GA		"Christensens Physics of Diagnostic Radiology," Curry et al., pp.29-33, 1990.	
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		-	APPLICANT	First Named Inventor	Glenn J. Leed	dy		
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	(Use as man	y sheets as	necessary)	Examiner Name	Shrinivas Rao			
Sheet	1	of	4	Attorney Docket Number	ELM-1 Cont.1	10		

		Document Number		ENT DOCUMENTS	Pages, Columns, Lines, Where
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Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁶ (# known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	70
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Sn		WO 1992 017901	10-15-1992	Integrated System Assemblies Corporation		
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				Art Unit	2814		
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		NON PATENT LITERATURE DOCUMENTS	
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO.	APPLICATION NO.
ELM-1 Cont. 10	10/700,429
APPLICANT Glenn J. Leedy	CONFIRMATION NO. 5639
FILING DATE	GROUP
November 3, 2003	3729

U.S. PATENT DOCUMENTS

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	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
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	3,997,381	12/14/76	Wanlass	156	3	
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1,	957,882	09/18/90	Shinomiya	438	65		
	65,415	10/23/90	Young et al.	200	83 N		
	966,663	10/30/90	Mauger	205	656		
	994,735	02/19/91	Leedy	324	158		
	008,619	04/16/91	Keogh et al.	324	207.17		
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5,0	20,219	06/04/91	Leedy	29	846		
	34,685	07/23/91	Leedy	324	158 F		
	70,026	12/03/91	Greenwald et al.	437	3		
	71,510	12/10/91	Findler et al.	156	647		
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7 5.1	132,244	07/21/92	Roy	438	477		

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A	5,151,775	09/29/92	Hadwin	357	80	
.	5,156,909	10/20/92	Henager, Jr. et al.	428	334	
	5,203,731	04/20/93	Zimmerman	445	24	
	5,225,771	07/06/93	Leedy	324	158	
	5,236,118	08/17/93	Bower et al.	228	193	
	5,262,351	11/16/93	Bureau et al.	437	183	
- 	5,270,261	12/14/93	Bertin et al.	437	209	
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	5,324,687	06/28/94	Wojnarowski	437	225	
	5,354,695	10/11/94	Leedy	438	411	
	5,363,021	11/08/94	MacDonald	315	366	
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	5,420,458	05/30/95	Shimoji	257	622	
	5,424,920	06/13/95	Miyake	361	735	
	5,426,072	06/20/95	Finnila	437	208	
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	5,432,729	07/11/95	Carson et al.	365	63	
	5,434,500	07/18/95	Hauck et al.	324	67	
	5,451,489	09/19/95	Leedy	430	313	·
	5,453,404	09/26/95	Leedy	437	203	
	5,457,879	10/17/95	Gurtler et al.	29	895	
	5,476,813	12/19/95	Naruse	437	132	
	5,489,554	02/06/96	Gates	437	208	
	5,502,667	03/26/96	Bertin et al.	365	51	
h	5,512,397	04/30/96	Leedy	430	30	
\$/	5,527,645	06/18/96	Pati et al.	430	5	

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Th	T = ====	1	I	1	T		
- 1-	5,529,829	06/25/96	Koskenmaki et al.	428	167		
	5,534,465	07/09/96	Frye et al.	437	209	`	
	5,555,212	09/10/96	Toshiaki et al.	365	200		
	5,563,084	10/08/96	Ramm et al.	437	51		
	5,571,741	11/05/96	Leedy	437	51		
	5,580,687	12/03/96	Leedy	430	5		
	5,581,498	12/03/96	Ludwig et al.	365	63	<u> </u>	
	5,582,939	12/10/96	Pierrat	430	5		
	5,583,688	12/10/96	Hornbeck	359	291		
	5,592,007	01/07/97	Leedy	257	347	<u> </u>	
	5,592,018	01/07/97	Leedy	257	619		
	5,595,933	01/21/97	Heijboer	439	20		
	5,606,186	02/25/97	Noda	257	226		
	5,627,112	05/06/97	Tennant et al.	438	113		
	5,629,137	05/13/97	Leedy	430	313		
	5,633,209	05/27/97	Leedy	435	228		
	5,637,536	06/10/97	Val	438	686		
	5,654,127	08/05/97	Leedy	430	315		
	5,654,220	08/05/97	Leedy	438	25		
	5,656,552	08/12/97	Hudak et al.	438	15 ~		
	5,675,185	10/07/97	Chen et al.	257	774		
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	5,725,995	03/10/98	Leedy	430	315		
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	5,760,478	06/02/98	Bozso et al.	257	777		
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	5,793,115	08/11/98	Zavracky et al.	257	777		
1	5,831,280	11/03/98	Ray	257	48		
1	5,834,334	11/10/98	Leedy	438	107		
1	5,840,593	11/24/98	Leedy	438	6	.	
Son	5,856,695	01/05/99	Ito et al.	257	370		

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6/	5,868,949	02/09/	00	Sotokaw	a et al	Т	216	18		<u> </u>	
-1	5,869,354	02/09/	$\overline{}$	Leedy	a et ai.	十	438	110	+-		
	5,870,176	02/09/		Sweatt e	t al	_	355	53			
	5,880,010	03/09/		Davidsor		十	438	455	_		
	5,882,532	03/16/		Field et a		\dashv	216	2			
	5,902,118	05/11/		Hübner	31.	\dashv	438	106	_		
	5,902,118	06/22/		Leedy		-	438	108	\dashv		
	5,946,559	08/31/		Leedy		\dashv	438	157	-		
	5,985,693	11/16/		Leedy	•	_	438	107			
	5,998,069	12/07/		Cutter et	al	\dashv	430	5			
	6,008,126	12/28/		Leedy	<u>a.</u>		438	667	\top		. •
	6,020,257	02/01/		Leedy		\dashv	438	626	_	•	
	6,045,625	04/04/		Houston		_	148	33.3			•
	6,084,284	07/04/		Adamic,			257	506	\dashv		
	6,097,096	08/01/		Gardner		_	257	777			
	6,133,640	10/17/		Leedy	Ct di.	寸	257	778			
	6,194,245 B1	02/27/		Tayanak		寸	438	57			
	6,197,456 B1	03/06/		Aleshin		_	430	5		<u> </u>	····
	6,208,545 B1	03/27/		Leedy	<u> </u>	_	365	51			
	6,236,602 B1	05/22/		Patti		$\neg \dagger$	365	201	_ _		
	6,261,728 B1	07/17/		Lin		_	430	30			
1	6,288,561 B1	09/11/		Leedy		\dashv	324	760	\top		
- 6	6,294,909 B1	09/25/	-	Leedy		$\neg \dagger$	324	207.17			
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ATTY. DOCKET NO.

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APPLICANTS
Glenn J. Leedy

FILING DATE
November 3, 2003

APPLN. NO.
10/700,429

CONF. NO.
5639

GROUP ART UNIT
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SORPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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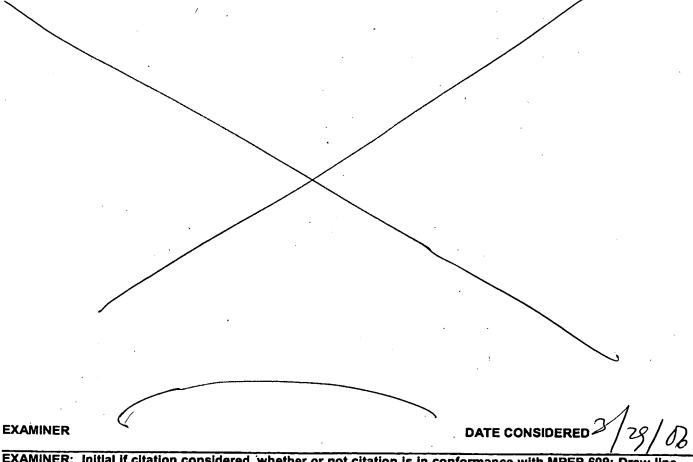
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